



MMBT5401

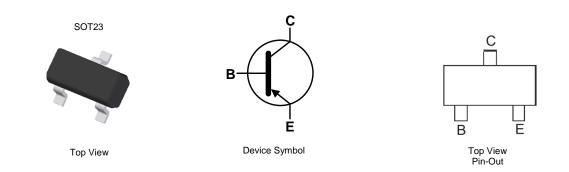
150V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type MMBT5551
- Ideal for Low Power Amplification and Switching
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208⁽²⁾
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel	
MMBT5401-7-F	AEC-Q101	K4M	7	8	3,000	
MMBT5401-13-F	AEC-Q101	K4M	13	8	10,000	
MMBT5401Q-7-F	Automotive	K4M	7	8	3,000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and

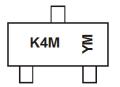
Lead-free. 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally

the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K4M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 3 = March)

Date Code Key

Year	2017	201	8 2	019	2020	2021	2022	2023	2024	20	25	2026
Code	E	F		G	Н		J	K	L	Ν	N	Ν
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-160	V
Collector-Emitter Voltage	V _{CEO}	-150	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	lc	-600	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	D	310	mW	
	(Note 7)	P _D	350		
Thermal Resistance Junction to Ambient	(Note 6)	D	403	0000	
Thermal Resistance, Junction to Ambient	(Note 7)	R _{eja}	357	°C/W	
Thermal Resistance, Junction to Leads (Note 8)		R _{0JL}	350	°C/W	
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to +150	°C		

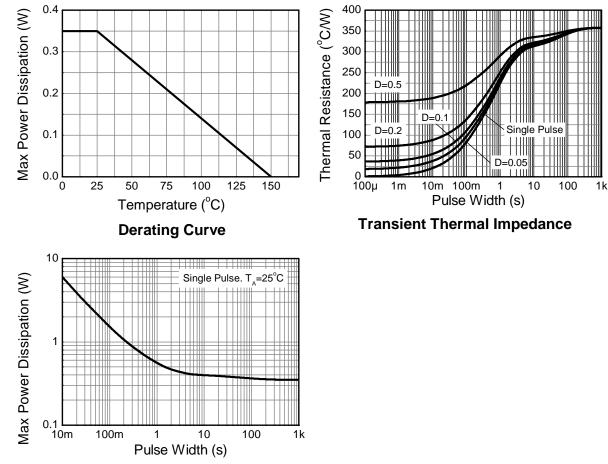
ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air Notes: For a device induited of minimum recommended paralytic to copper that is a conditions whilst operating in a steady-state.
Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
Thermal resistance from junction to solder-point (at the end of the leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 10)			1		
Collector-Base Breakdown Voltage	BV _{CBO}	-160	_	V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-150		V	$I_{C} = -1mA, I_{B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5		V	$I_E = -100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}		-50 -50	nA µA	$V_{CB} = -120V, I_E = 0$ $V_{CB} = -120V, I_E = 0, T_A = +100^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	-50	nA	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)					
		50			$I_{C} = -1mA, V_{CE} = -5V$
DC Current Gain	h _{FE}	60	240	—	$I_{C} = -10 \text{mA}, V_{CE} = -5 \text{V}$
		50			$I_{C} = -50 \text{mA}, V_{CE} = -5 \text{V}$
Collector-Emitter Saturation Voltage	Manua -		-0.2	V	$I_{C} = -10mA$, $I_{B} = -1mA$
	V _{CE(SAT)}		-0.5		$I_{C} = -50 \text{mA}, I_{B} = -5 \text{mA}$
Base-Emitter Saturation Voltage			1	V	$I_{C} = -10mA$, $I_{B} = -1mA$
	V _{BE(SAT)}				$I_{C} = -50 \text{mA}, I_{B} = -5 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	_	6	pF	$V_{CB} = -10V, f = 1MHz, I_E = 0$
Small Signal Current Gain	h _{fe}	40	260	—	$V_{CE} = -10V$, $I_C = -1mA$, f = 1kHz
Current Gain-Bandwidth Product	fT	100	300	MHz	$V_{CE} = -10V, I_C = -10mA,$ f = 100MHz
Noise Figure	NF	_	8.0	dB	$V_{CE} = -5V, I_C = -200\mu A,$ $R_S = 10\Omega, f = 1kHz$

Notes: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



 $T_A = -50^{\circ}C$

1,000

100

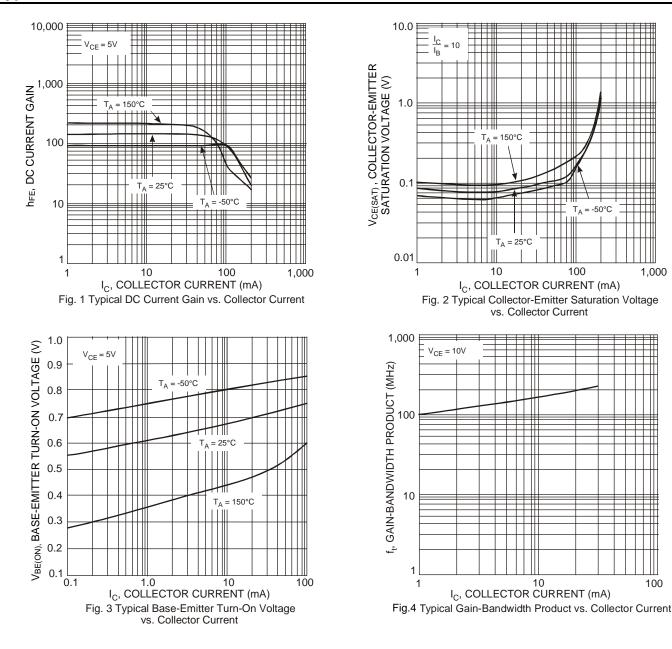
100

 $T_A = 150^{\circ}C$

 $T_A = 25^{\circ}C$

10

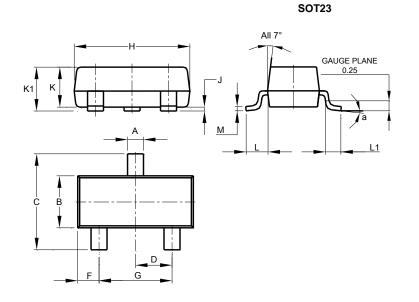
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

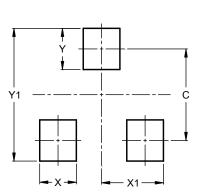
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
К	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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